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(12) **United States Design Patent**
Okuyama et al.

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(54) **SEMICONDUCTOR ELEMENT**

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(**) Term: **14 Years**

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(51) **LOC (7) Cl.** **13-03**

(52) **U.S. Cl.** **D13/182**

(58) **Field of Search** D13/182; D14/172,
D14/212, 233; 117/95; 216/227; 257/146,
618; 313/309, 310, 327, 336; 369/112.08,
112.09; 438/460

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(List continued on next page.)

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(57) **CLAIM**

The ornamental design for a semiconductor element, as shown and described.

DESCRIPTION

FIG. 1 is a top, front perspective view of a semiconductor element showing our new design;

FIG. 2 is a front elevational view thereof;

FIG. 3 is a rear elevational view thereof;

FIG. 4 is a right side elevational view thereof;

FIG. 5 is a left side elevational view thereof;

FIG. 6 is a top plan view thereof; and

FIG. 7 is a front elevational view of another embodiment of a semiconductor element, which is transparent, showing our new design;

FIG. 8 is a rear elevational view thereof;

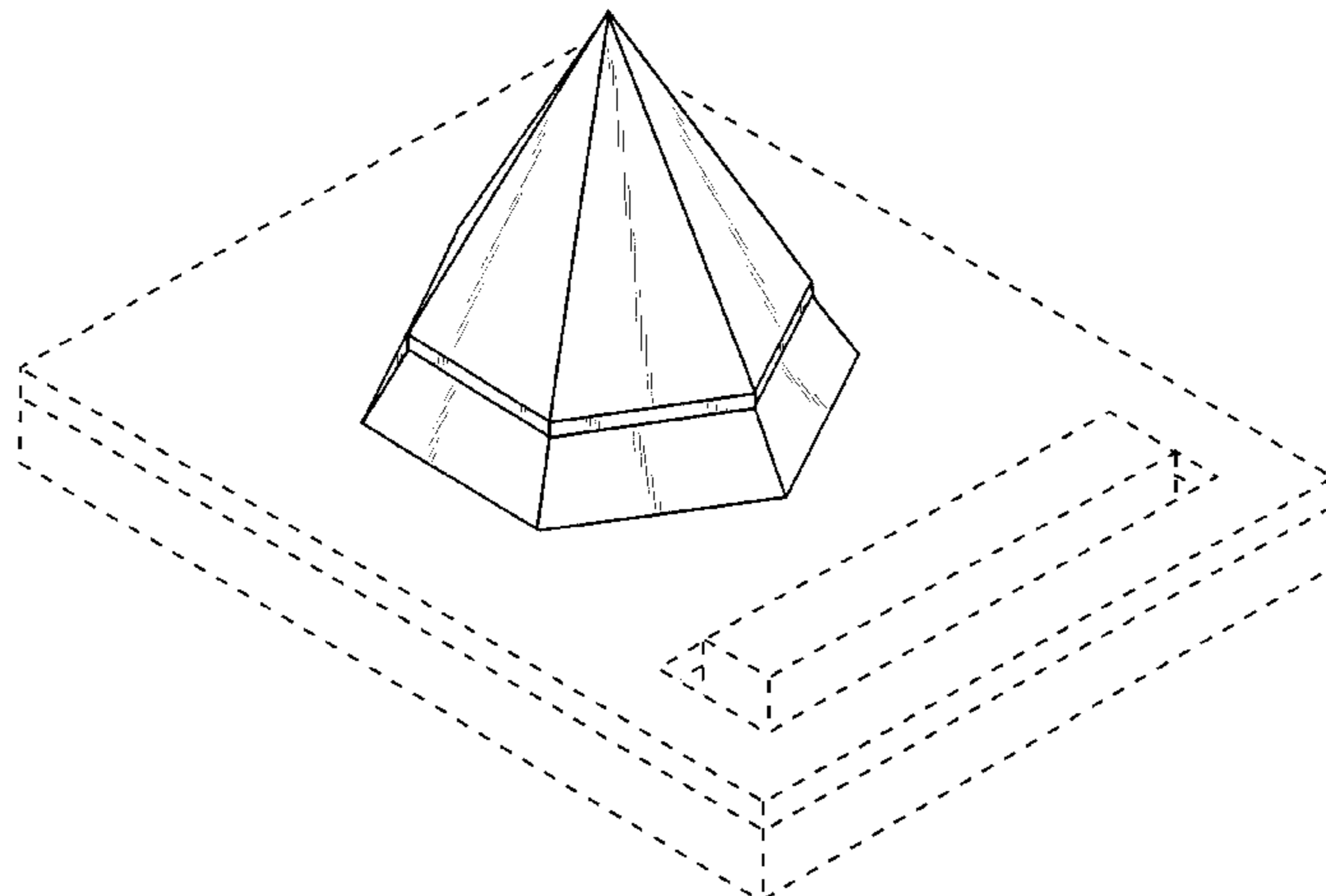
FIG. 9 is a right side elevational view thereof;

FIG. 10 is a left side elevational view thereof; and,

FIG. 11 is a top plan view thereof, a bottom plan view thereof being a mirror image.

Portions in broken lines are for illustrative purposes only and form no part of claimed design.

1 Claim, 7 Drawing Sheets



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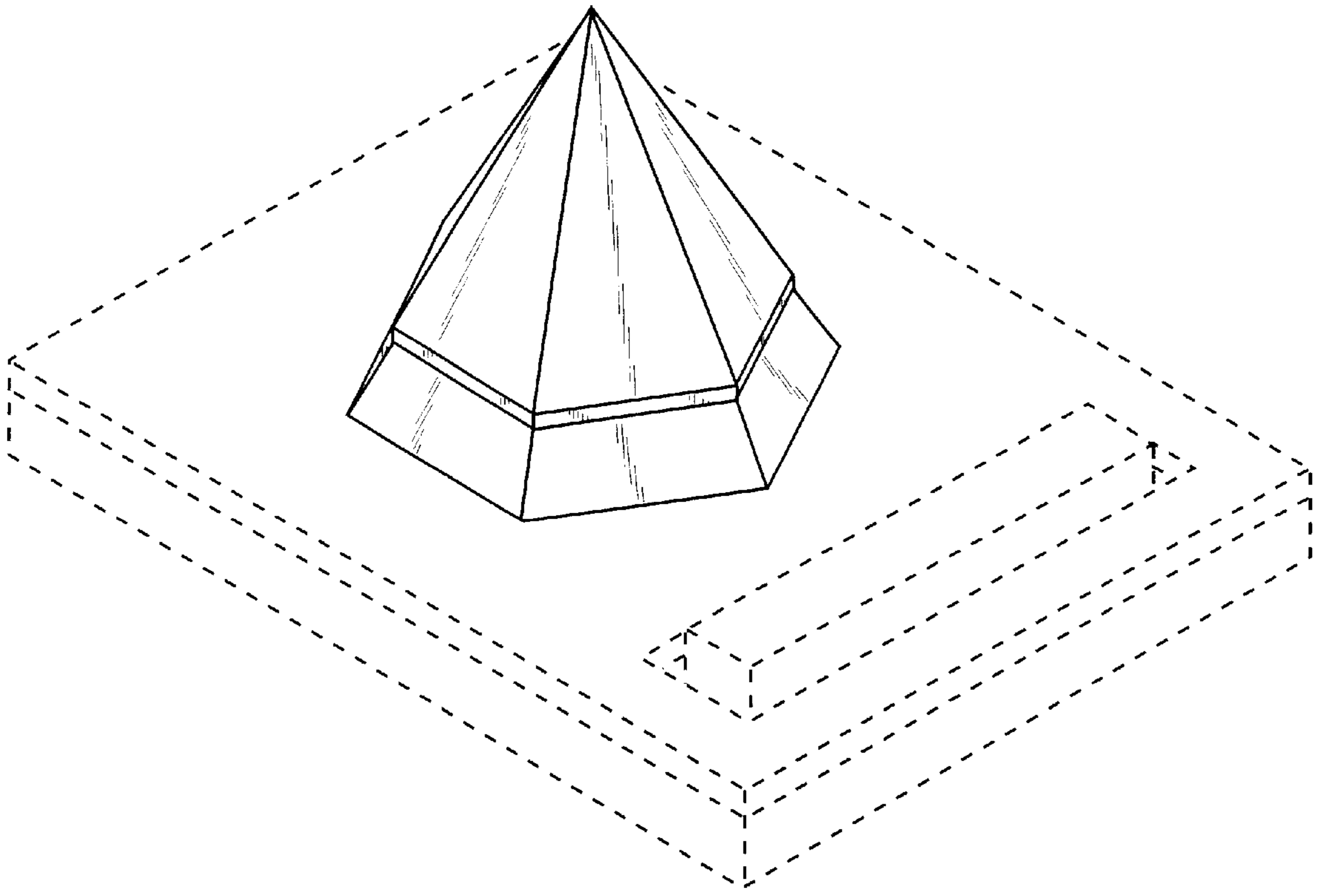


Fig. 1

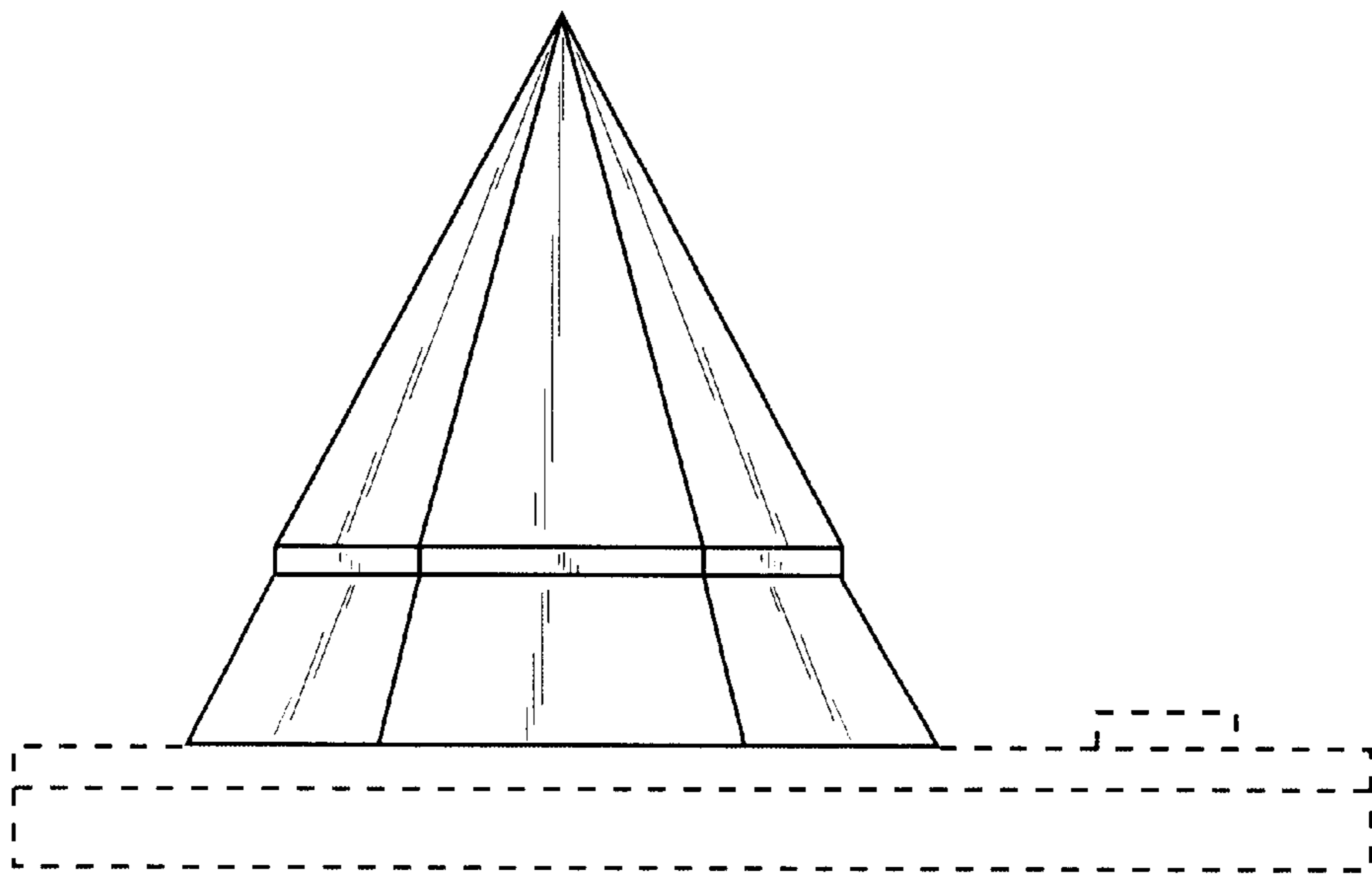


Fig. 2

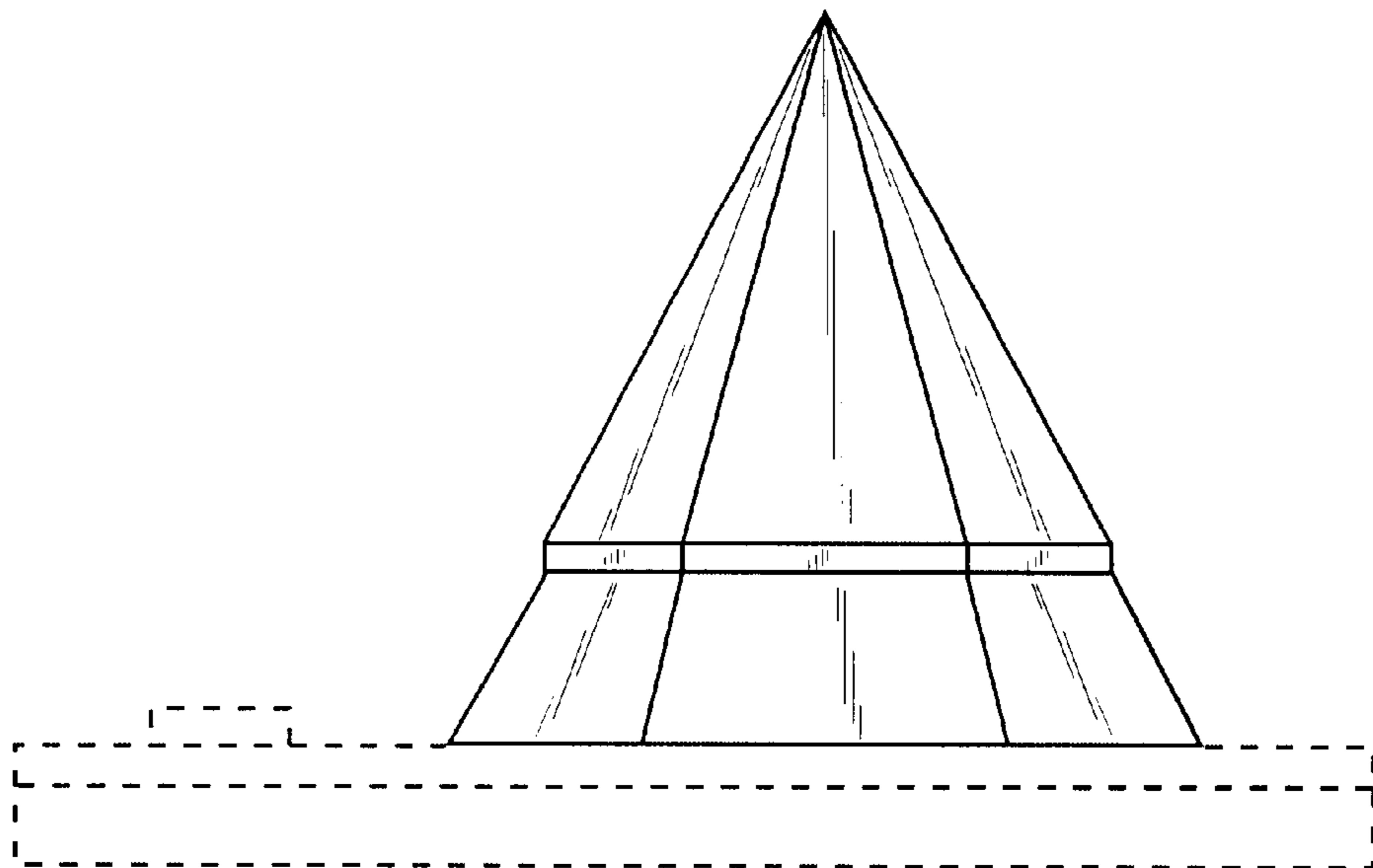


Fig. 3

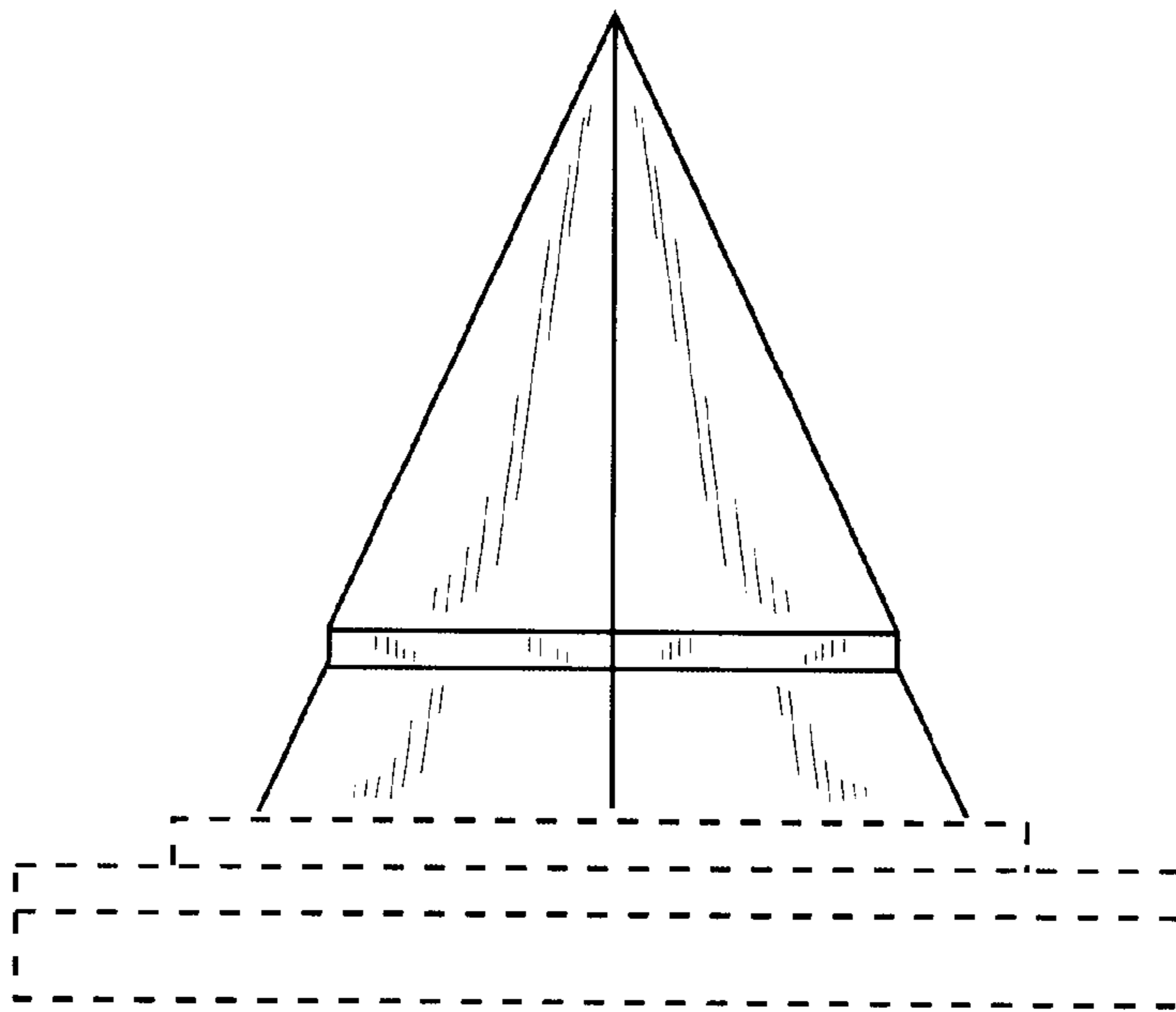


Fig. 4

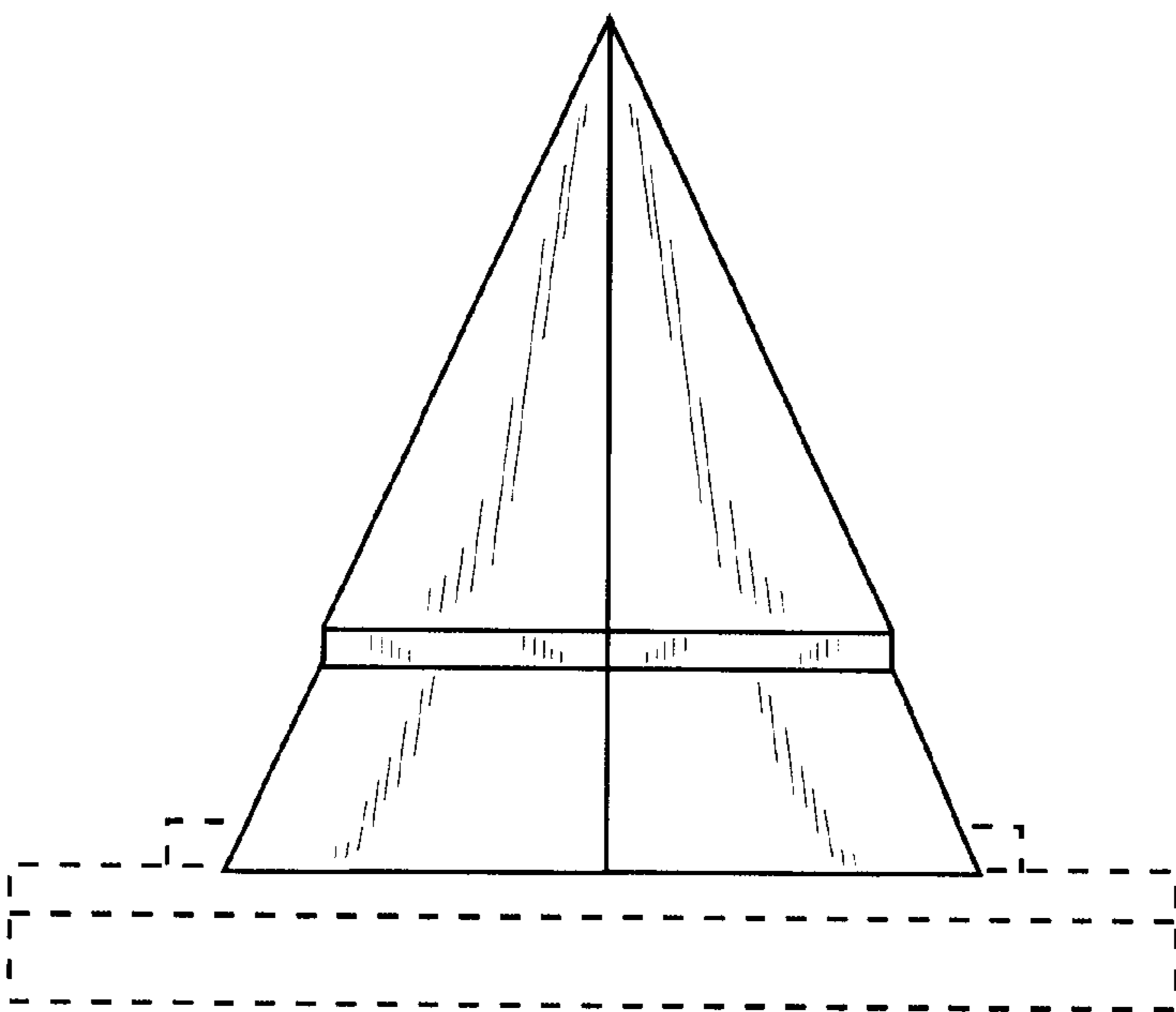


Fig. 5

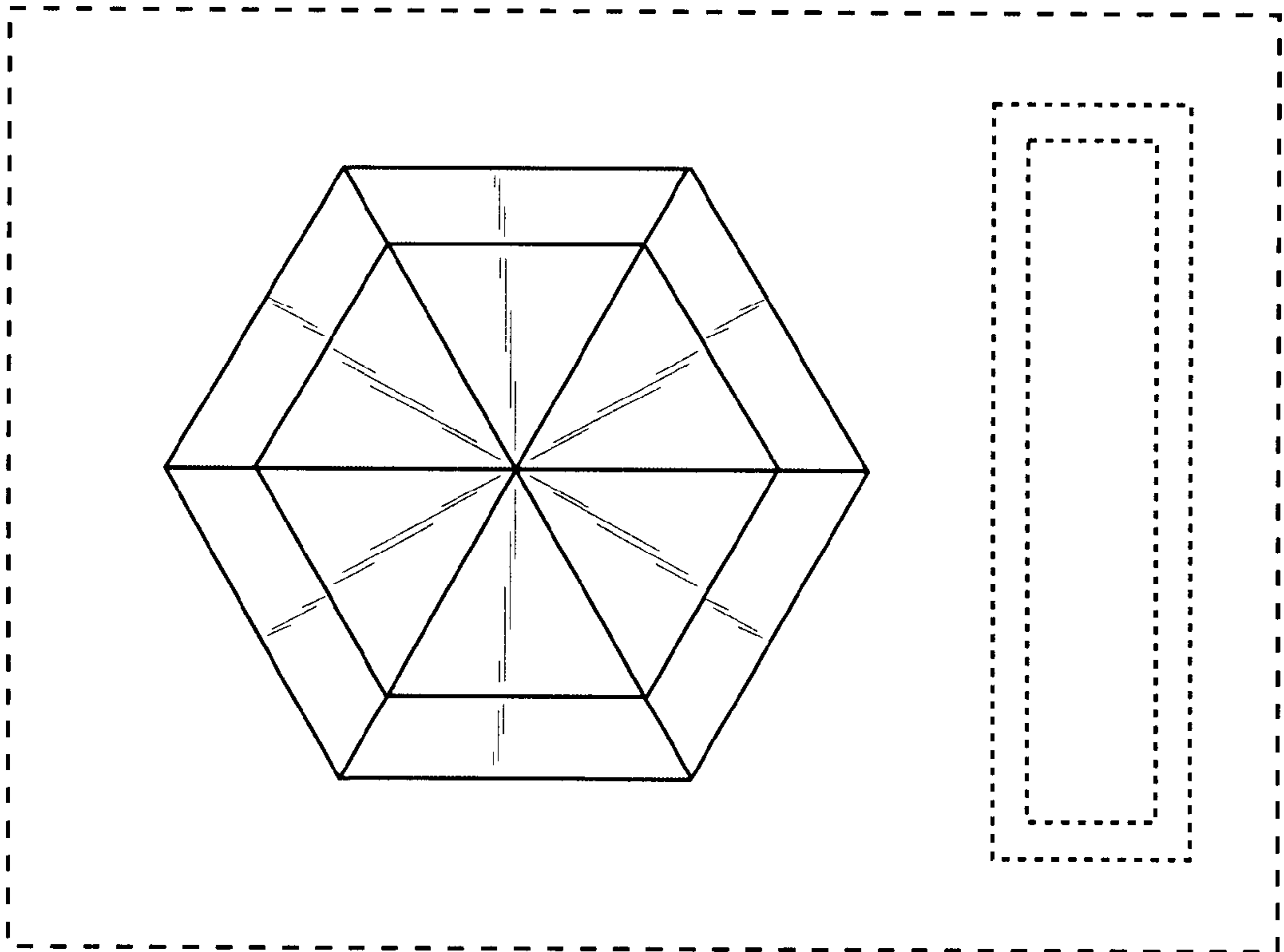


Fig. 6

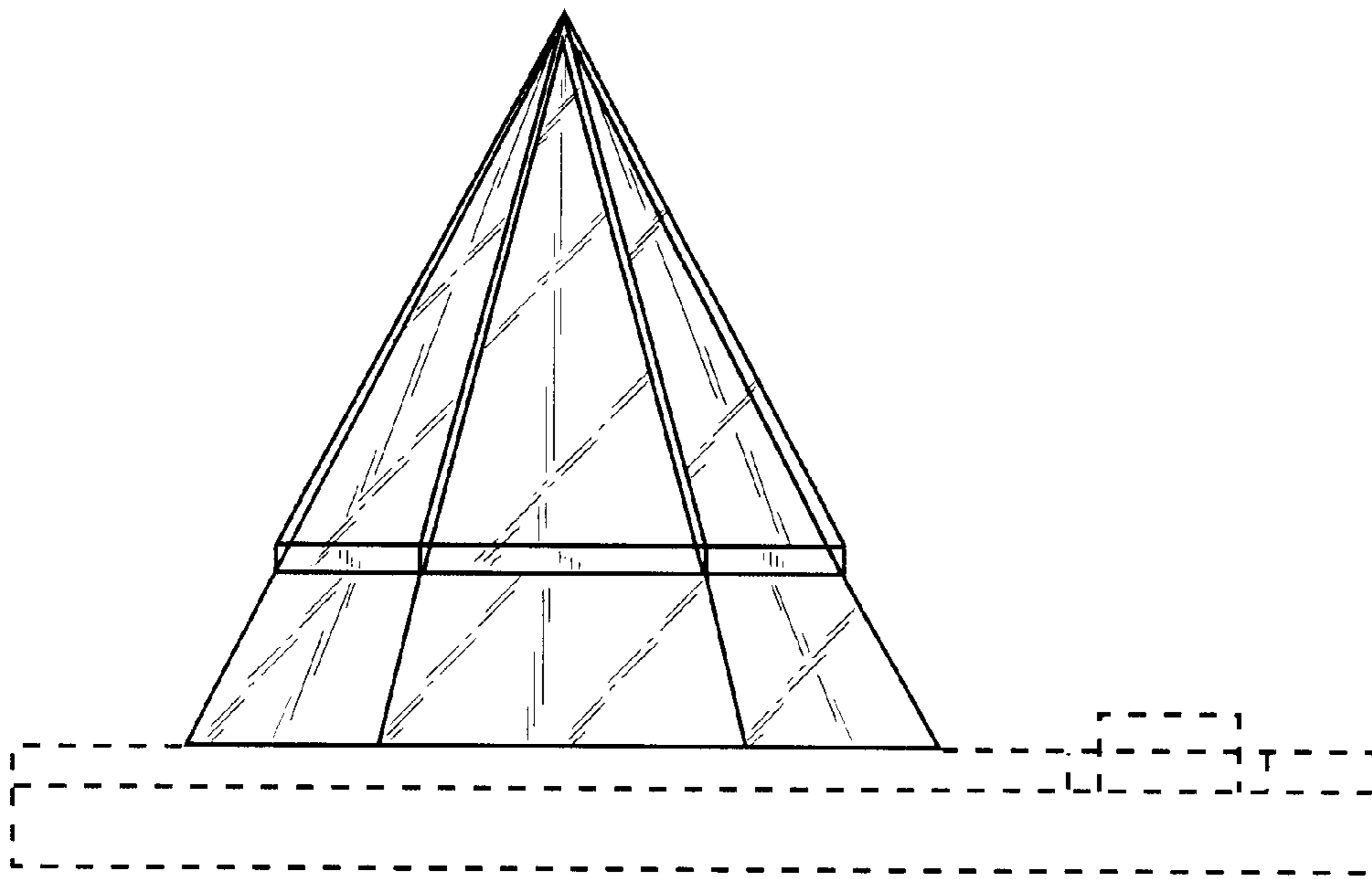


Fig. 7

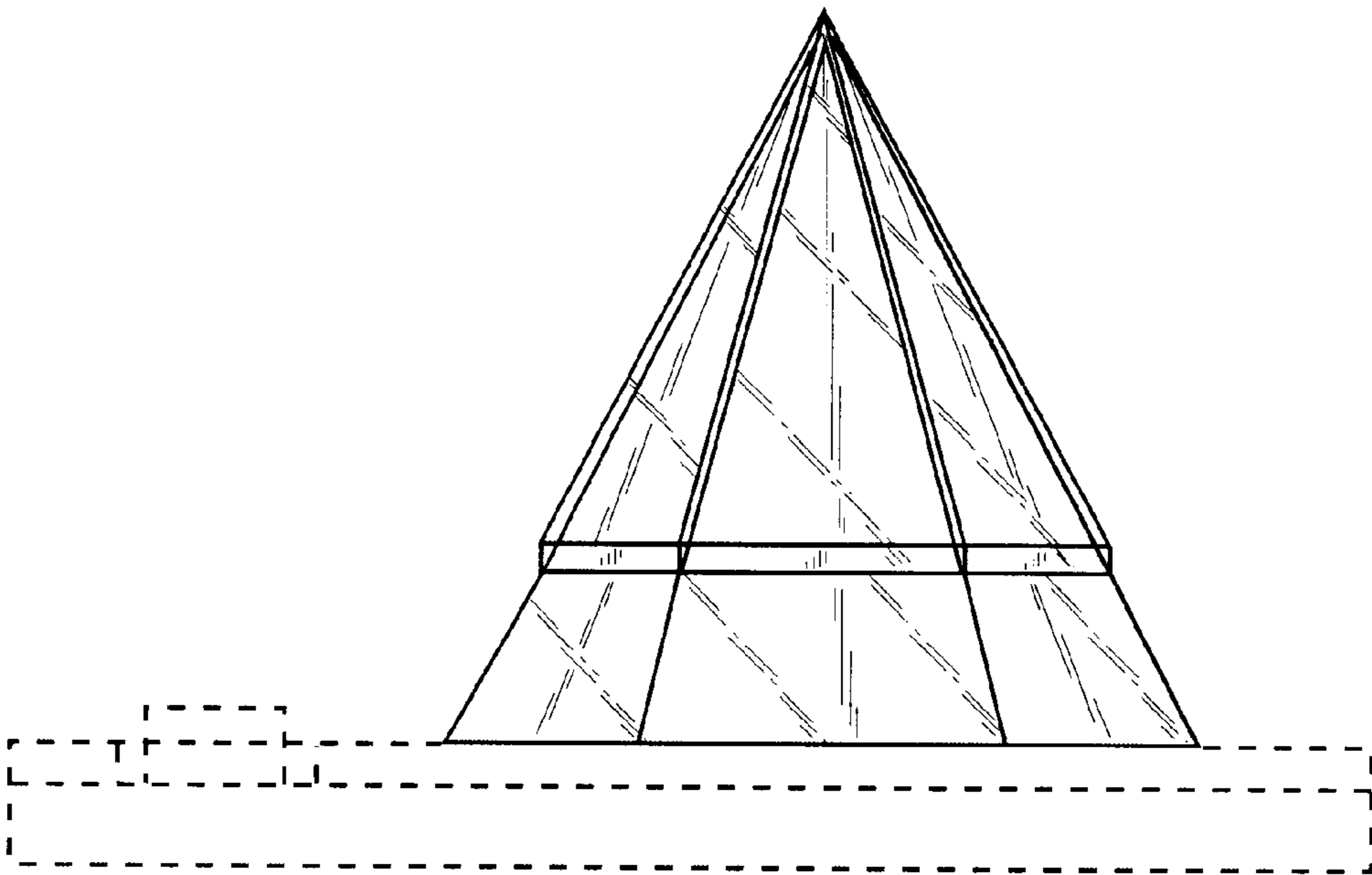


Fig. 8

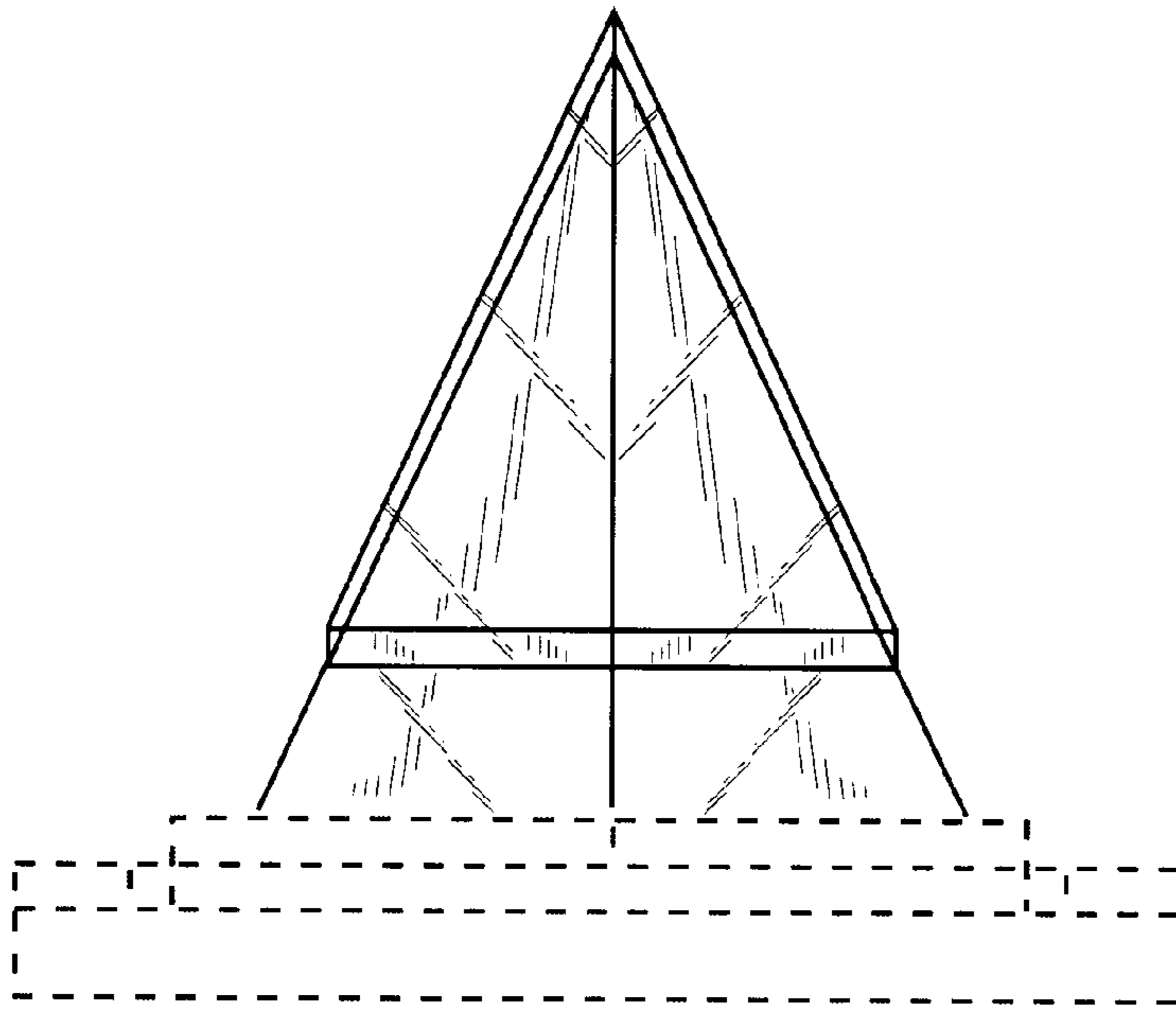


Fig. 9

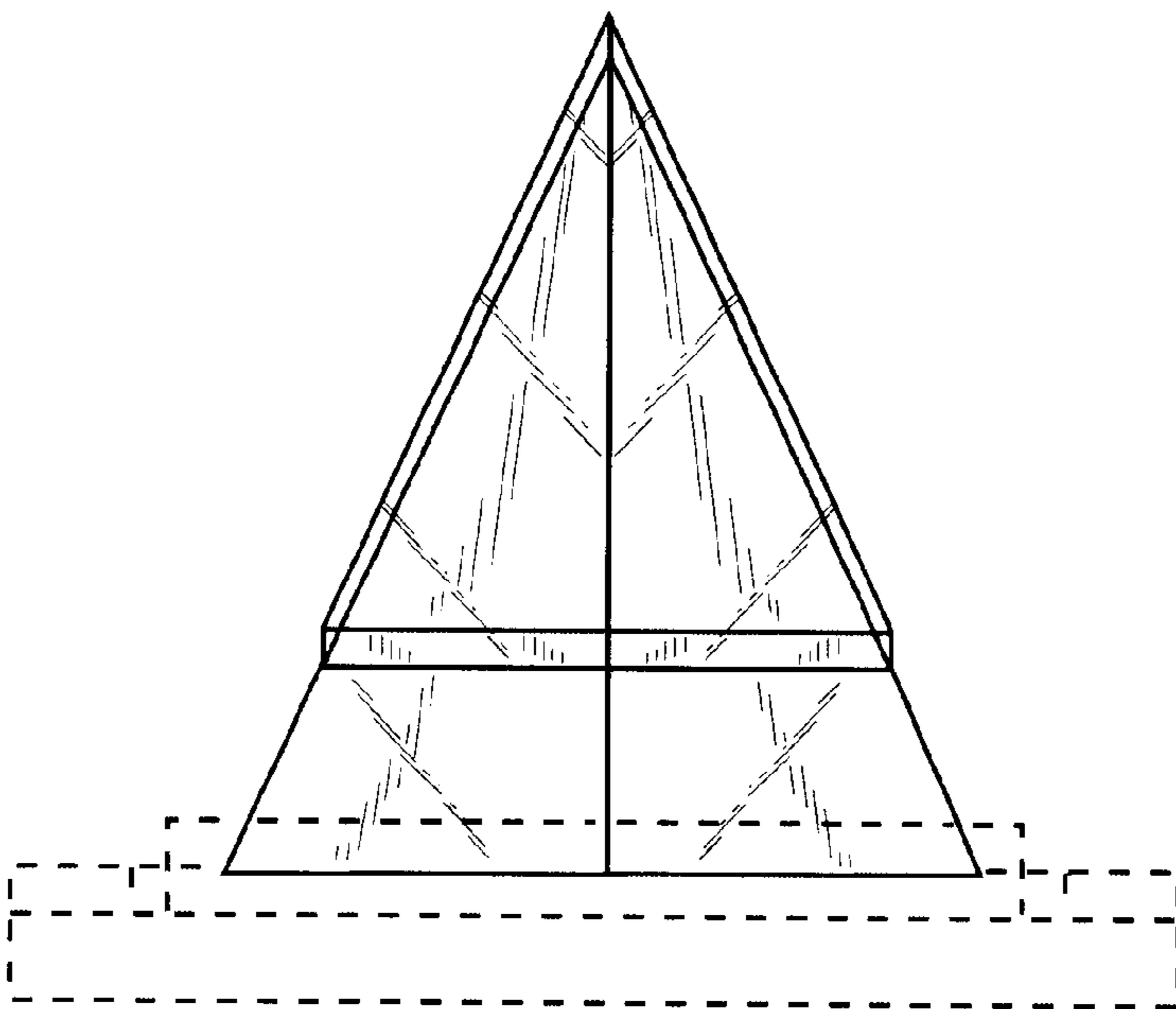


Fig. 10

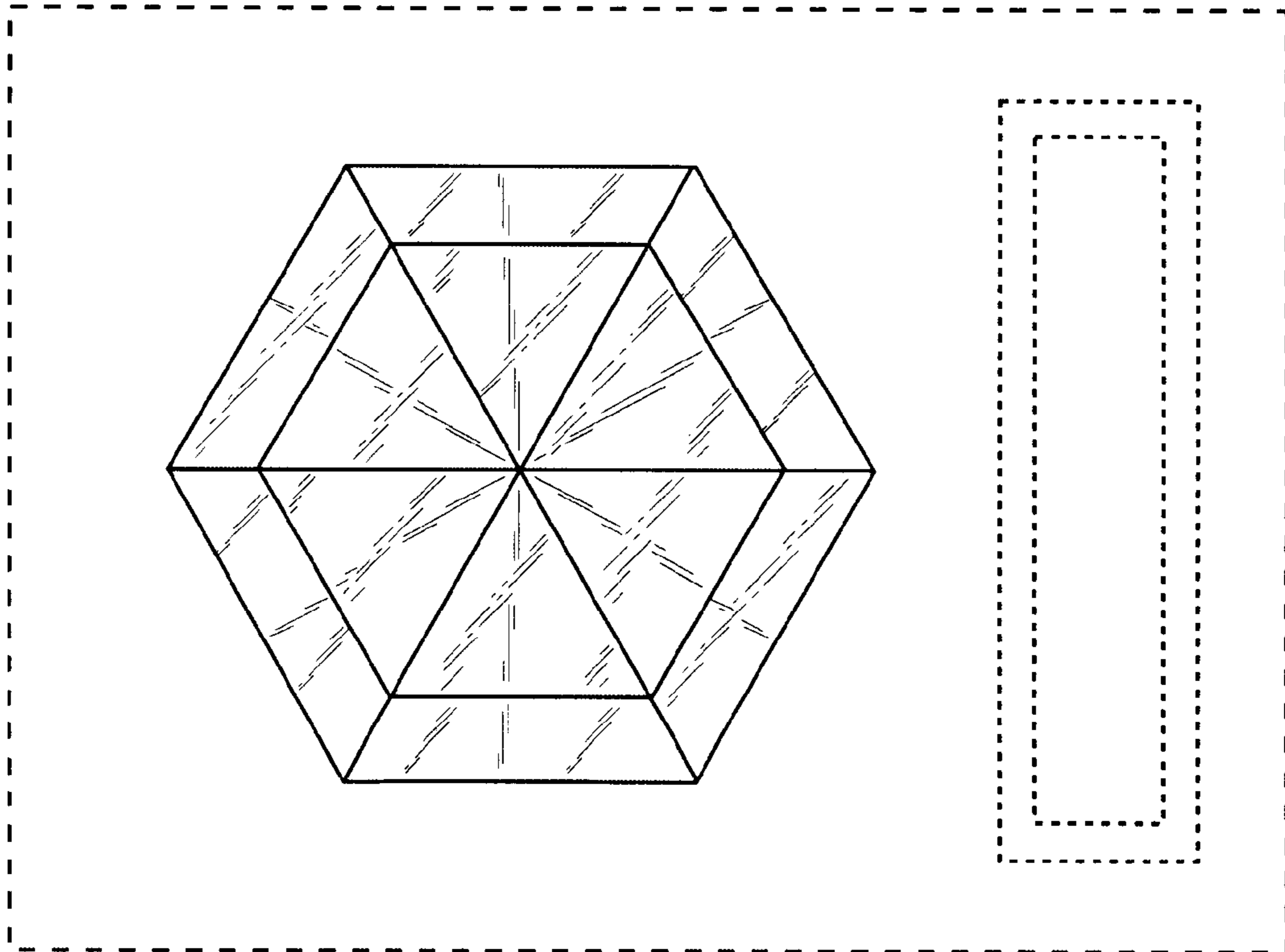


Fig. 11